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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/694,660	10/27/2003	Timothy Lance Blankenship	08211/0200250-US0/P05707	4239
38845	7590	01/14/2005		
DARBY & DARBY P.C. P.O. BOX 5257 NEW YORK, NY 10150-5257			EXAMINER TAN, VIBOL	
			ART UNIT 2819	PAPER NUMBER

DATE MAILED: 01/14/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary

Application No.

10/694,660

Applicant(s)

BLANKENSHIP, TIMOTHY LANCE

Examiner

Vibol Tan

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-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --
Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 27 October 2003.
2a) ☐ This action is **FINAL**. 2b) ☒ This action is non-final.
3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1-20 is/are pending in the application.
4a) Of the above claim(s) _____ is/are withdrawn from consideration.
5) ☐ Claim(s) _____ is/are allowed.
6) ☒ Claim(s) 1-5 and 8-20 is/are rejected.
7) ☒ Claim(s) 6 and 7 is/are objected to.
8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
10) ☐ The drawing(s) filed on _____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
a) ☐ All b) ☐ Some * c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
2. ☐ Certified copies of the priority documents have been received in Application No. _____.
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- 1) ☒ Notice of References Cited (PTO-892)
2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
3) ☒ Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)
Paper No(s)/Mail Date 2/10/04.
4) ☐ Interview Summary (PTO-413)
Paper No(s)/Mail Date. _____.
5) ☐ Notice of Informal Patent Application (PTO-152)
6) ☐ Other: _____.

DETAILED ACTION

Claim Rejections - 35 USC § 102

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

2. Claims 1-5 and 8-20 are rejected under 35 U.S.C. 102(b) as being anticipated by Nebel (U. S. PAT. 6,392,440).

In claims 1 and 2, Nebel teaches all claimed features in Fig. 1, an input level translator circuit comprising: a first pass circuit (MP1) that is coupled to a full-range node (IN), to a first bias node (5), and to a high-range node (P1); a second pass circuit (MN1) that is coupled to the full-range node (IN), to a second bias node (6), and to a low-range node (N1); a first shunt circuit (MP21-MP22) that is coupled between the first bias node (5) and the high-range node (P1); and a second shunt circuit (MN21-MN22) that is coupled between the second bias node (6) and the low-range node (N1); wherein the first bias node and the second bias node coincide.

In claim 3, Nebel further teaches the input level translator circuit of claim 1, wherein the first shunt circuit (MP22) is configured to receive a first cascode bias voltage (LOW) at the first bias node (5), wherein the first cascode bias voltage is appropriate for biasing a cascode transistor (MP21).

In claim 4, Nebel further teaches the input level translator circuit of claim 1, wherein the first pass circuit (MP1) is configured to provide a high-range signal (5.0v) at

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the high-range node (P1) in response to a full-range signal (IN), the second pass circuit (MN1) is configured to provide a low-range signal (0v) at the low-range node (6) in response to the full-range signal, the full-range signal has a range from a low-voltage level (0v) to a high-voltage level (5.0v), the low-range signal has a range from the low-voltage level (0v) to an intermediate-voltage level (3.3v), the high-range signal has a range from the intermediate-voltage level (3.3v) to the high-voltage level (5.0v), and the intermediate voltage level is partway between the low-voltage level and the high-voltage level ($0v < 3.3v < 5.0v$).

In claim 5, Nebel further teaches the input level translator circuit of claim 1, wherein: the first bias node (5) is coupled to a gate of a p-type transistor (MP22) configured to operate as a cascode transistor (MP22), and the second bias node (6) is coupled to a gate of an n-type transistor (MN22) configured to operate as another cascode transistor (MN22).

In claim 8, Nebel further teaches the input level translator circuit of claim 1, wherein the first shunt circuit (MP21-MP22) is configured to influence a resistance between the first bias node (5) and the high-range node (P1) depending on a full-range signal (IN).

In claim 9, Nebel further teaches the input level translator circuit of claim 8, wherein the first shunt circuit (MP21-MP22) is configured to isolate (disengage) the first bias node (5) from the high-range node (P1) if the full-range signal (IN) corresponds to a first logic level (logic 1).

In claim 10, Nebel further teaches the input level translator circuit of claim 8, wherein the first shunt circuit (MP21-MP22) is configured to short (connect) the first bias node (5) to the high-range node (P1) if the full-range signal (IN) corresponds to a second logic level (0V).

In claim 11, Nebel further teaches the input level translator circuit of claim 1, wherein the second shunt circuit (MN21-MN22) is configured to influence a resistance between the second bias node (6) and the low-range node (N1) depending on a full-range signal (IN).

In claim 12, Nebel further teaches the input level translator circuit of claim 1, wherein the first shunt circuit (MP21-MP22) is configured to short (connect) the high-range node (P1) to the first bias node (5) when a full-range signal (IN) corresponds to a first logic level (logic 0), and isolate (disconnect) the high-range node from the first bias node when the full-range signal corresponds to a second logic level (logic 1), and the second shunt (MN21-MN22) circuit is configured to short the low-range node (6) to the second bias node (N1) when a full-range signal (IN) corresponds to the second logic level (logic 1), and isolate the low-range node from the second bias node when the full-range signal corresponds to the second logic level (logic 0).

Method claims 13-16 correspond to detailed circuitry already discussed similarly with regard to claims 1-5 and 8-12.

Claims 17-19 correspond to detailed circuitry already discussed similarly with regard to claims 1-5 and 8-12.

Claim 20 corresponds to detailed circuitry already discussed similarly with regard to claim 1.

3. Claims 6 and 7 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Vibol Tan whose telephone number is (571) 272-1811. The examiner can normally be reached on Monday-Friday (7:00 AM-4:30 PM).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Mike J. Tokar can be reached on (571) 272-1812. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).



VIBOL TAN
PRIMARY EXAMINER